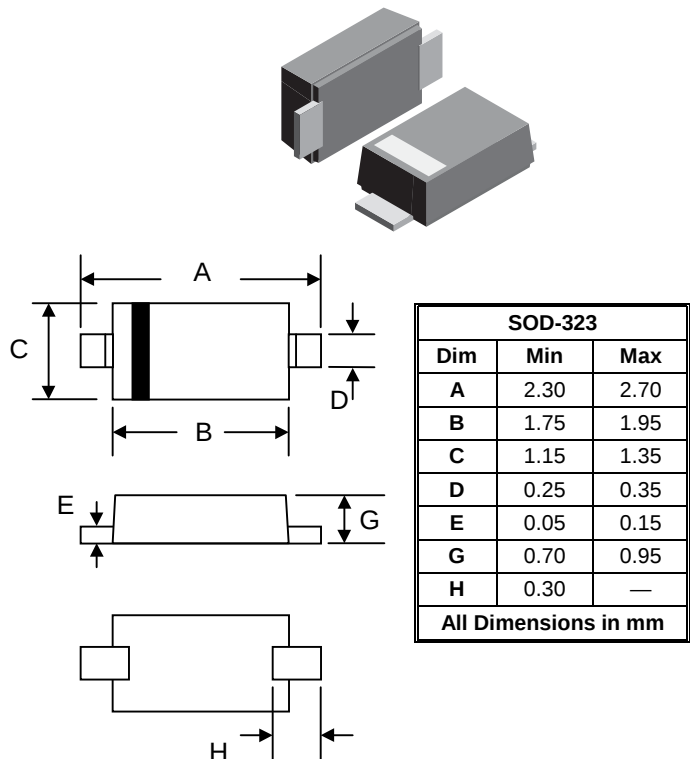


Features

- Silicon Epitaxial Planar Diode
- Fast switching diode, especially suited for applications requiring high voltage capability

Mechanical Data

- Case: SOD-323, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.004 grams (approx.)
- Marking: A3



Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Continuous reverse voltage		V_R	240	V
Peak repetitive reverse voltage		V_{RRM}	300	V
Forward current (continuous)		I_F	225	mA
Peak repetitive forward current		I_{FRM}	625	mA
Non-repetitive peak forward current	$t_p = 1 \mu\text{s}$	I_{FSM}	4.0	A
	$t_p = 1 \text{ s}$	I_{FSM}	1.0	A
Power dissipation		P_{tot}	200 ¹⁾	mW

¹⁾ Device on Fiberglass Substrate, see layout on second page

Thermal Characteristics $T_{amb} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Typical thermal resistance junction to ambient air		R_{thJA}	650 ¹⁾	$^\circ\text{C/W}$
Junction temperature		T_j	150	$^\circ\text{C}$
Storage temperature range		T_S	- 65 to + 150	$^\circ\text{C}$

¹⁾ Device on Fiberglass Substrate, see layout on second page

Electrical Characteristics $T_{amb} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Reverse breakdown voltage	$I_R = 100 \mu\text{A}$	V_{BR}	300			V
Leakage current	$V_R = 240 \text{ V}$	I_R			100	nA
	$V_R = 240 \text{ V}, T_j = 150^\circ\text{C}$	I_R			100	μA
Forward voltage	$I_F = 20 \text{ mA}$	V_F		0.83	0.87	V
	$I_F = 100 \text{ mA}$	V_F			1.00	V
Diode capacitance	$V_F = V_R = 0, f = 1 \text{ MHz}$	C_{tot}			5.0	pF
Reverse recovery time	$I_F = I_R = 30 \text{ mA}, I_{rr} = 3.0 \text{ mA}, R_L = 100 \Omega$	t_{rr}			50	ns

¹⁾ Device on Fiberglass Substrate, see layout